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(54) **Manufacturing method for reflection type liquid crystal display**

(57) On an insulating substrate (10), there are formed a first gate electrode (11), a gate insulating film (12), a semiconductor film (13), and an interlayer insulating film (15). Above the interlayer insulating film (15), a TFT is formed having a second gate electrode (17) connected to the first gate electrode (11). Then, a photosensitive resin (70) is formed over the entire surface

of the extant layers. Subsequently, first exposure (75) is applied using a first mask (71), and second exposure (76) is then applied using a second mask (72) with a larger amount of light than used for the first exposure. The second mask (72) has an opening at a position corresponding to a source (13s). Thereafter, the photosensitive resin film (70) is developed thereby forming a contact hole (73) and a recess (74).

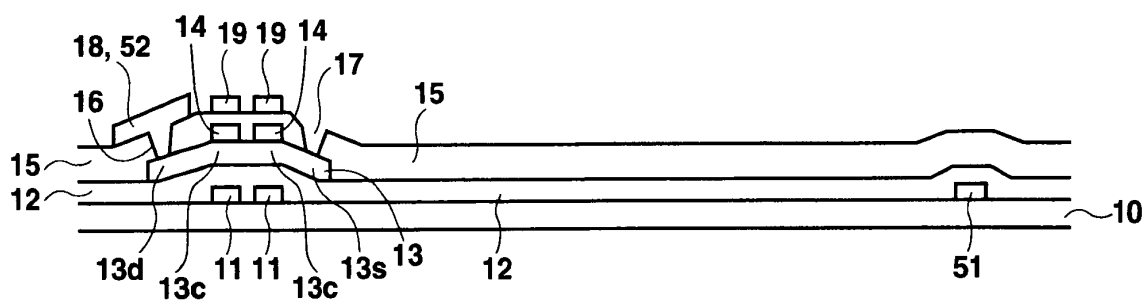


Fig. 1(a)

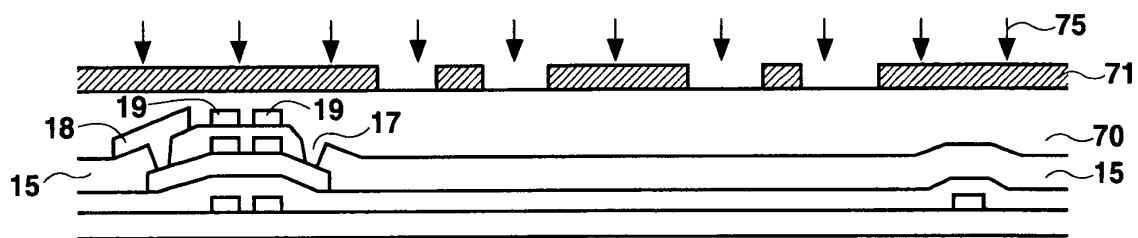


Fig. 1(b)

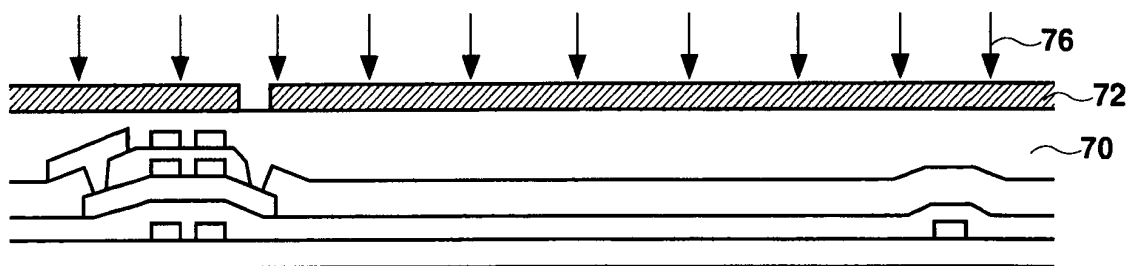


Fig. 1(c)

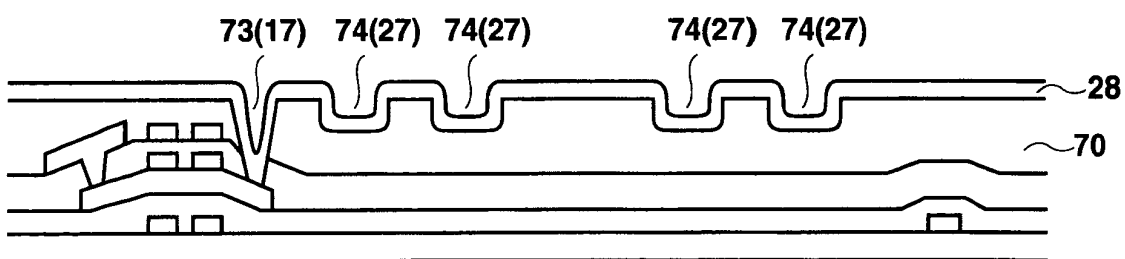


Fig. 1(d)

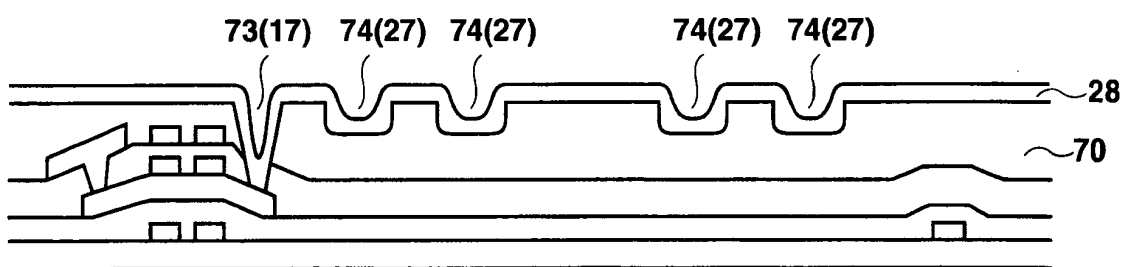


Fig. 1(e)

Description

BACKGROUND OF THE INVENTION

1. Field of the Invention:

[0001] The present invention relates to a reflection type liquid crystal display.

2. Description of the Related Art:

[0002] In recent years, a reflection type liquid crystal display (LCD) has been developed in which incident light from an observer side is reflected by a reflective display electrode so that display is observed.

[0003] Fig. 2 is a plan view showing a display pixel and nearby area of an example of the above mentioned reflective type LCD. Fig. 3 is a cross sectional view, along the line A-A in Fig. 2, showing manufacturing steps.

[0004] As shown in Fig. 2, a TFT is formed in an area close to a crossing point between a gate signal line 51 and a drain signal line 52. The gate signal line 51 includes a gate electrode 11 and supplies a gate signal to a gate, while the drain signal line 52 includes a drain electrode 16 and supplies a drain signal to a drain. The gate 11 of the TFT is connected to the gate signal line 51. The drain 13d is connected to the drain signal line 52, while the source 13s is connected to a reflection display electrode 28.

[0005] The reflection display electrode 28 preferably has an uneven surface, rather than an even surface, so that incident light can be reflected in multiple directions. With such an arrangement, the display of the reflection type LCD (Liquid Crystal Display) can be observed from a larger area, so that a larger viewing angle can be ensured.

[0006] Referring to Figs. 3(a) to 3(d), an example of manufacturing steps for the above described reflection type LCD will be described.

[0007] Step 1 (Fig. 3(a)): on an insulating substrate 10, there are sequentially formed a first gate electrode 11, a gate insulating film 12, and an active layer 13, wherein the insulating substrate 10 comprises a quartz glass, a non-alkali glass, and so on, the first gate electrode 11 comprises a refractory metal (Cr, Mo, and so on), the gate insulating film 12 comprises a SiN film and a SiO₂ film, and the active layer 13 comprises an island-shaped polycrystalline silicon film.

[0008] Then, in the active layer 13, there are formed a channel 13c above the first gate electrode 11, and a source 13s and a drain 13d at the respective sides of the channel 13c, wherein the source 13s and the drain 13d are formed through ion implantation.

[0009] Further, on the channel 13c, there is formed a stopper insulating film 14, comprising a SiO₂ film, as a mask covering the channel 13c for preventing ion intrusion at the time of ion implantation.

[0010] Covering the entire surface of the gate insulating film 12, the active layer 13, and the stopper insulating film 14, there is formed an interlayer insulating film 15, comprising laminated SiO₂ film, SiN film and SiO₂ film.

5 [0011] Then, contact holes 16, 17 are made in the interlayer insulating film 15 at respective positions corresponding to the drain 13d and the source 13s. The contact hole 16, corresponding to the drain 13d, is filled by metal, specifically, by a single Al layer or sequentially laminated Mo and Al layers, thereby forming a drain electrode 18. At the same time of the formation of the drain electrode 18, a second gate electrode 19 is formed on the interlayer insulating film 15 above the channel 13c using metal, specifically, a single Al layer or sequentially laminated Mo and Al layers. Note that nothing is filled in the contact hole 17.

10 [0012] The second gate electrode 19 is connected to the gate signal line 51 on the insulating substrate 10, via a contact hole 20, formed in the gate insulating film 12 and the interlayer insulating film 15 as shown in Fig. 1. A drain signal line 52 is formed on the interlayer insulating film 15.

15 [0013] Step 2 (Fig. 3(b)): a first planarization insulating film 21, made of organic resin, and so on, is formed over the layers formed at Step 1, and a first resist film 22 is applied thereon. Thereafter, exposure and development processes are applied using a first mask 23, which has an opening at a position corresponding to the contact hole 17, followed by etching the first planarization insulating film 21, thereby forming a contact hole 24 corresponding to the contact hole 17.

20 [0014] Step 3 (Fig. 3(c)): a second planarization insulating film 25 is formed on the semiconductor film 13 in the contact hole 24 and the exposed first planarization insulating film 21. A second resist film 26 is then applied on the film 25. Thereafter, exposure and development processes are applied using a second mask 32, which has an opening at a position corresponding to a recess 27 (29) which is to be formed on an area, on the second planarization insulating film 25, where a reflection display electrode 28 is to be formed, and the second planarization insulating film 25 is thereafter etched whereby a concave 29 (27) is formed (Fig. 3(d)).

25 [0015] With the second resist film 26 subsequently removed, a contact hole 24, where the reflection display electrode 28 contacts the source 13s, is formed, and so are concaves 29 (27) in the reflection display electrode formation area. With the above, the reflection display electrode 28 resultantly has an uneven surface. As a result, incident light can be reflected in multiple directions, and a wider viewing angle can thus be achieved.

30 [0016] However, the above described manufacturing method of a reflection type LCD may result in increased costs and labor as it initially requires formation of a contact hole 24 in the first planarization insulating film 21, and then formation of a second planarization insulating film 25 in a different manufacturing step for subsequent formation of a concave 29 (27) therein.

SUMMARY OF THE INVENTION

[0017] The present invention aims to provide an efficient method for manufacturing a reflection type LCD having a concave in a reflection film.

[0018] According to the present invention, two exposures are applied to a photosensitive resin, using two different masks, before development, whereby two types of concaves each having different depths are formed. This enables reduction of the number of steps in formation of concave with two different depths.

[0019] In particular, a concave with one of the two depths is used to constitute a contact hole for connection between a TFT transistor and a reflection film (a reflection electrode) having a size corresponding to a pixel, and a concave with another depth is used as a concave in the reflection electrode.

BRIEF DESCRIPTION OF THE DRAWINGS

[0020] The above and other objects, features, and advantages of the present invention will become further apparent from the following description of the preferred embodiment taken in conjunction with the accompanying drawings wherein:

Figs. 1(a), 1(b), 1(c), 1(d), 1(e) are cross sectional views showing manufacturing steps for a reflection type LCD in a preferred embodiment of the present invention;

Fig. 2 is a plan view showing a reflection type LCD in the preferred embodiment of the present invention;

Figs. 3(a), 3(b), 3(c), 3(d) are cross sectional view showing manufacturing steps for a conventional reflection type LCD; and

Figs. 4(a), 4(b), 4(c), 4(d), 4(e) are cross sectional view showing manufacturing steps for a reflection type LCD in another preferred embodiment of the present invention.

DESCRIPTION OF THE PREFERRED EMBODIMENTS

[0021] In the following, a manufacturing method for a reflection type LCD according to the present invention will be described.

[0022] Figs. 1(a) to 1(e) are cross sectional views, along the line A-A in Fig. 2, showing manufacturing steps for a reflection type LCD of the present invention.

[0023] As shown in Fig. 2, a TFT is formed in an area close to a crossing point between a gate signal line 51 and a drain signal line 52. The gate signal line 51 includes a first gate electrode 11, while the drain signal line 52 includes a drain electrode 16. A reflection display electrode 28, which comprises reflection material, is connected to the TFT. The reflection display electrode 28 is provided extending above the TFT, and has a sur-

face with concaves 27 formed thereon.

[0024] Step 1 (Fig. 1(a)): on an insulating substrate 10, there are sequentially formed a first gate electrode 11, a gate insulating film 12, and an active layer 13, wherein the insulating substrate 10 comprises a quartz glass, a non-alkali glass, and so on, the first gate electrode 11 constitutes a part of the gate signal line 51 and comprises refractory metal (Cr, Mo, and so on), the gate insulating film 12 comprises a SiN film and a SiO₂ film, and the active layer 13 comprises a polycrystalline silicon film.

[0025] In the active layer 13, there are formed a channel 13c above the first gate electrode 11, and a source 13s and a drain 13d at the respective sides of the channel 13c. The source 13s and the drain 13d are formed through ion implantation.

[0026] On the channel 13c, there is formed a stopper insulating film 14, comprising a SiO₂ film, as a mask covering the channel 13c for preventing ion intrusion at the time of ion implantation.

[0027] Covering the entire surface of the gate insulating film 12, the active layer 13, and the stopper insulating film 14, there is formed an interlayer insulating film 15, which comprises laminated SiO₂ film, SiN film and SiO₂ film. The interlayer insulating film 15 may be formed of either a single layer of organic material such as SiO, SiN, acrylic, and so on, or multiple layers of combinations of any thereof.

[0028] Then, contact holes 16, 17 are formed in the interlayer insulating film 15 at respective positions corresponding to the drain 13d and the source 13s. The contact hole 16, corresponding to the drain 13d, is filled by metal, specifically, by a single Al layer or sequentially laminated Mo and Al layers, thereby forming a drain electrode 18. At the same time as formation of the drain electrode 18, a second gate electrode 19 is formed on the interlayer insulating film 15 above the channel 13c. That is, a second gate electrode 19 is formed using metal such as a single Al layer or laminated Mo and Al layers.

[0029] The second gate electrode 19 is connected to the gate signal line 51 on the insulating substrate 10, via a contact hole 20, formed in the gate insulating film 12 and the interlayer insulating film 15.

[0030] A drain signal line 52 is formed on the interlayer insulating film 15 at the same time as formation of the drain electrode 18, which constitutes a part of the drain signal line 52.

[0031] Step 2 (Fig. 1(b)): a photosensitive resin film 70, made of insulating resin having photosensitivity and an even surface, is formed over the entire surface of the interlayer insulating film 15, including the contact hole 17, the drain signal line 52, the drain electrode 18, and the second gate electrode 19. Thereafter, a first mask 71 having an opening at a position corresponding to a recess 27 to be formed on an area where a reflection display electrode 28 is to be formed, is placed before first exposure 75 is applied. The amount of exposure is

determined such that the light reaches a point at a shallow depth below the surface of the photosensitive resin 70, specifically, 20 mJ/cm² to 60 mJ/cm², preferably 25 mJ/cm² to 50 mJ/cm², and more preferably 30 mJ/cm² to 40 mJ/cm².

[0032] Note that specific examples of photosensitive resin may be acrylic resin or polyimide.

[0033] Step 3 (Fig. 1(c)): the first mask 71 is removed, and a second mask 72 is placed instead. The second mask 72 has an opening at a position corresponding to a place where a contact hole 73 for connection between the source 13s of the active layer 13 and the reflection display electrode 28 is to be formed.

[0034] After the deposition of the second mask 72, second exposure 76 is applied. The amount of the second exposure is larger than that for the first exposure so that a deeper contact hole 73 than the concave 74 can be formed. That is, in order for the exposure light to reach deeper, specifically, deep enough to form a contact hole 73 reaching the source 13s, the amount of second exposure 76 must be large enough, specifically, 200 mJ/cm² to 600 mJ/cm², preferably 250 mJ/cm² to 500 mJ/cm², more preferably, 300 mJ/cm² to 400 mJ/cm².

[0035] Step 4 (Fig. 1(d)): after the second mask 72 is removed, the photosensitive resin film 70 is developed whereby a concave 74 and a contact hole 73 are formed.

[0036] After the formation of the concave 74 and the contact hole 73 as described above, a reflection display electrode 28, made of reflection material such as Al, is formed thereon. With the above, the contact hole 17 (corresponding to 73 in Fig. 1) and the concave 27 (corresponding to 74 in Fig. 1) are completed.

[0037] In addition, an alignment layer for aligning liquid crystal is formed on the reflection display electrode 28. Formation of the alignment film completes a TFT substrate. Then, opposing the TFT substrate, an opposing electrode substrate is formed, which has an opposing electrode and an alignment layer formed on the side thereof having liquid crystal, and a retardation film and a polarizer formed on the other side thereof without liquid crystal (i.e., on the observer side). The TFT substrate and the opposing electrode substrate are attached to each other along the edges thereof and liquid crystal is filled into the space between them, so that a reflection type LCD is completed.

[0038] It should be noted that the opposing electrode substrate is substantially transparent, and is not segmented for every pixel.

[0039] As described above, the use of photosensitive resin and exposure with the photosensitive resin using different amounts of light for formation of a desired contact hole and a concave, readily enable formation of a contact hole and a concave without the need of two formations of a planarization insulating film, as is conventionally needed. Therefore, the manufacturing process can be simplified, and costs can be reduced.

[0040] It should be noted that the present invention is not limited to the above embodiment, in which a concave

and a contact hole are formed by development. Moreover, heating at, e.g., about 220 °C after the development would make more gently slanting edges of the concave 74, as shown in Fig. 1 (e), so that a brighter display with incident light reflected in many more different directions can be obtained.

[0041] Also, the present invention is not limited to the above embodiment, in which concaves 27 are formed as two analogous rectangles formed in a reflection display electrode formation area, and the concave 27 may rather be formed in a circle or in two or more different shapes instead. Moreover, the number of the concave 27 is not limited to two, as described above, and a single concave 27 or three or more concaves 27 may be formed instead.

[0042] Further, the area where the concave 27 is formed is not limited to an area enclosed by the gate signal line 51 and the drain signal line 52, and the concave 27 may rather be formed in an area overlapping the gate signal line 51 or the drain signal line 52.

[0043] Still further, the present invention is not limited to the above embodiment, in which the circumferential edges of adjacent reflection display electrodes 28 overlap the gate signal line 51 and the drain signal line 52, and the edge may rather overlap either one of the gate signal line 51 and the drain signal line 52 or may even not overlap the signal line. Yet further, the reflection display electrode 28 may not extend over the TFT.

[0044] Moreover, the insulating film between the second gate electrode 17 and the active layer 13, i.e., the stopper insulating film 14, the interlayer insulating film 15, and the planarization insulating film 19 in this embodiment, may each be constituted of a single SiO₂, SiN, or any organic film, or a laminated combination thereof.

[0045] Also, instead of the above described TFT having a double gate electrode structure, having two gates, a single gate structure, having one gate, or a multiple gate structure, having two or more gates, may be similarly applicable.

[0046] The order of formation of the contact hole 72 and the recess 74 may be reversed from that shown in Figs. 1(a) to 1(e), into that shown in Figs. 4(a) to 4(e). With the reversed order, exposure for formation of the contact hole 73, as shown in Fig. 4(b), is initially applied, followed by exposure for formation of the recess 74, as shown in Fig. 4(c). In this case, Figs. 4(a), 4(d), 4(e) are identical to Figs. 1(a), 1(d), 1(e), Fig. 4(b) is identical to Fig. 1(c), and Fig. 4(c) is identical to Fig. 1(b).

[0047] As described above, according to the present invention, the number of formation steps may be reduced to readily attain contact between the reflection display electrode and the source, while a recess can be formed in a reflection display electrode formation area.

Claims

1. A manufacturing method for a reflection type liquid

crystal display having a reflection film for reflecting light having passed through a liquid crystal layer, comprising the steps of:

forming a photosensitive resin film on a substrate; 5
 exposing the photosensitive resin film with a first amount of light via a first mask;
 exposing the photosensitive resin film with a second amount of light via a second mask; 10
 developing the photosensitive resin film subjected to two exposures thereby forming two types of concaves having different depths; and
 forming a film using reflective material on the photosensitive resin developed to have two types of concaves, thereby forming the reflection film. 15

2. A manufacturing method according to claim 1, further comprising the step of forming a thin film transistor on the substrate so that the photosensitive resin film is formed thereon, 20
 wherein

the photosensitive resin film constitutes an insulating film, 25
 the reflection film is a reflection electrode having a size corresponding to a pixel, and
 the reflection electrode is electrically connected to the thin film transistor. 30

3. A manufacturing method according to claim 2, wherein

the first amount of light is larger than the second amount of light, 35
 the concave formed using the first mask constitutes a contact hole for electrically connecting the reflection electrode and the thin film transistor, and 40
 the concave formed using the second mask constitutes a concave formed on a surface of the reflection electrode.

4. A manufacturing method according to claim 2, wherein 45

the second amount of light is larger than the first amount of light, 50
 the concave formed using the first mask constitutes a concave formed on a surface of the reflection electrode, and
 the concave formed using the second mask constitutes a contact hole for electrically connecting the reflection electrode and the thin film transistor. 55

5. A manufacturing method according to any one of

claims 1 to 4, further comprising

after the step of developing the photosensitive resin film, a step of heating to give edges of the concave a gentler slope.

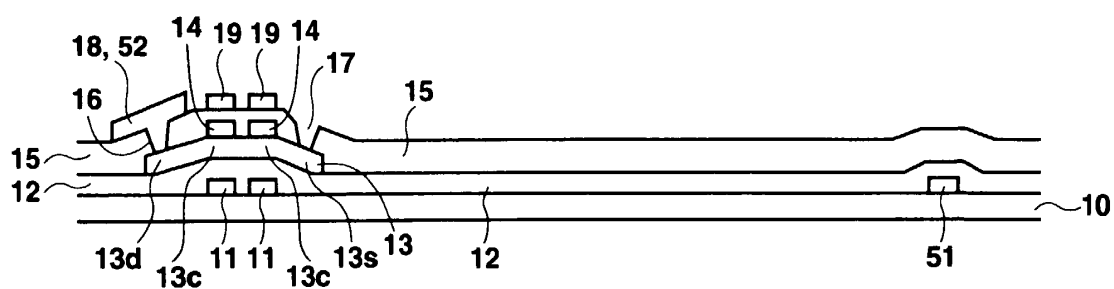


Fig. 1(a)

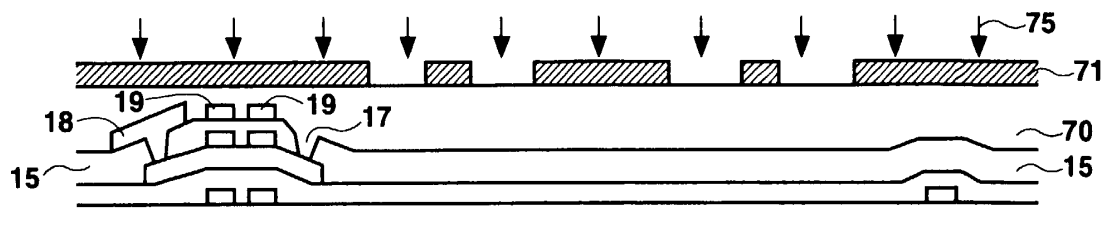


Fig. 1(b)

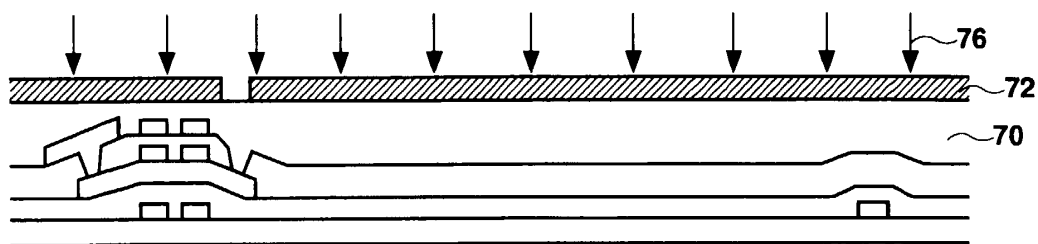


Fig. 1(c)

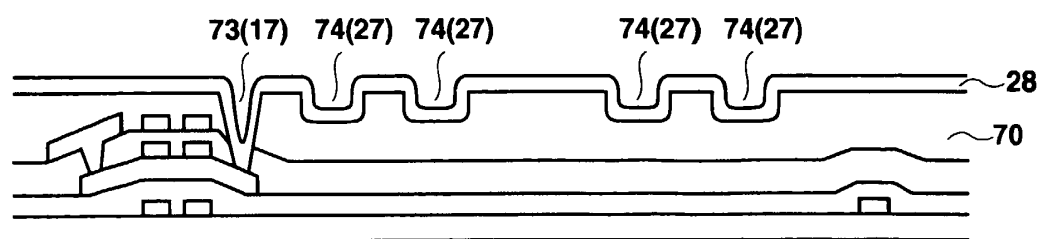


Fig. 1(d)

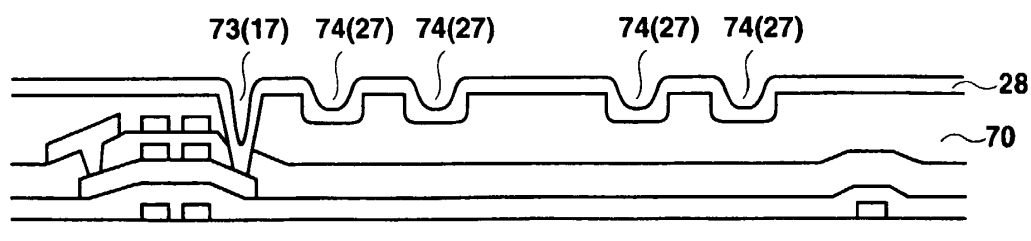


Fig. 1(e)

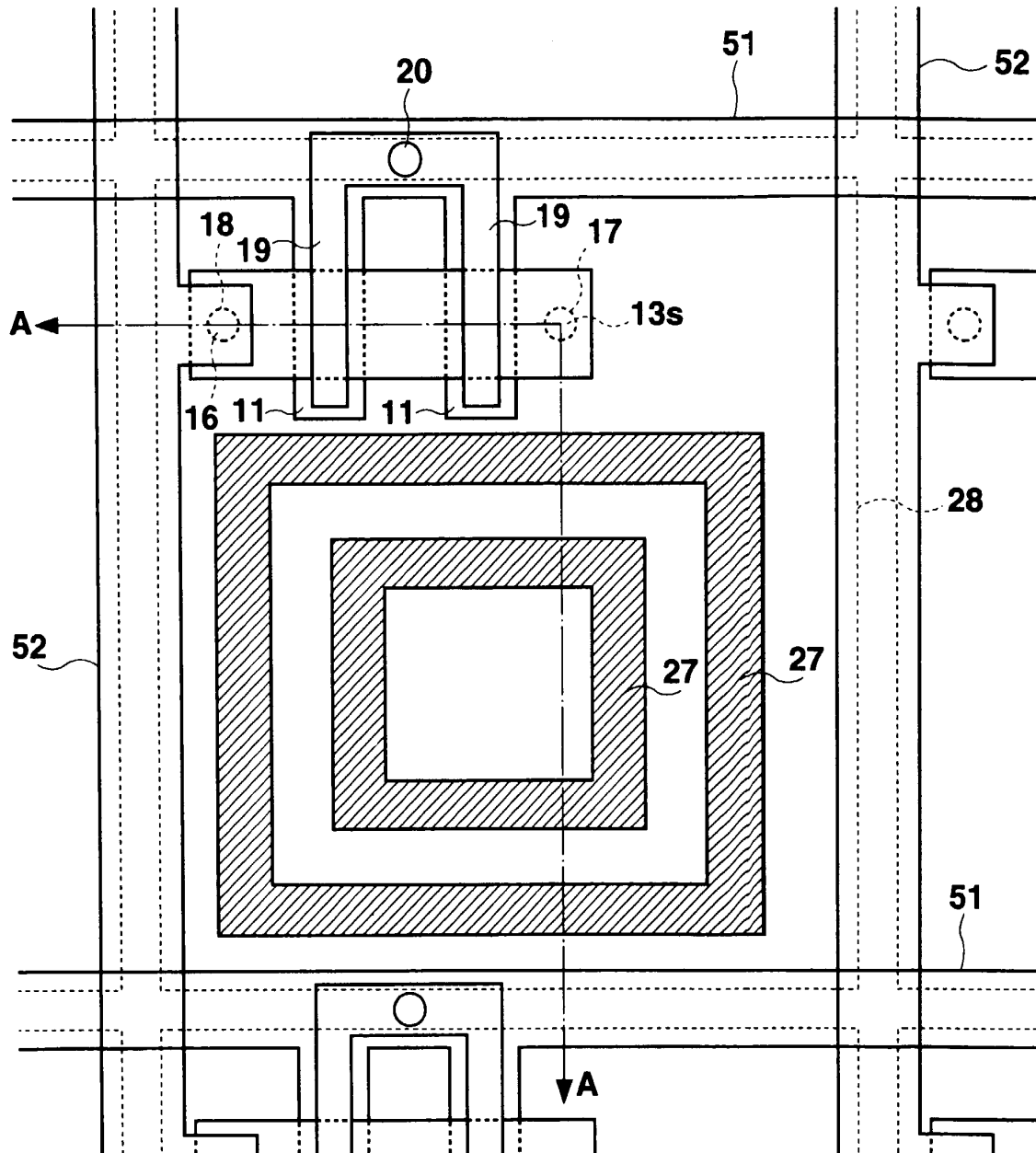


Fig. 2

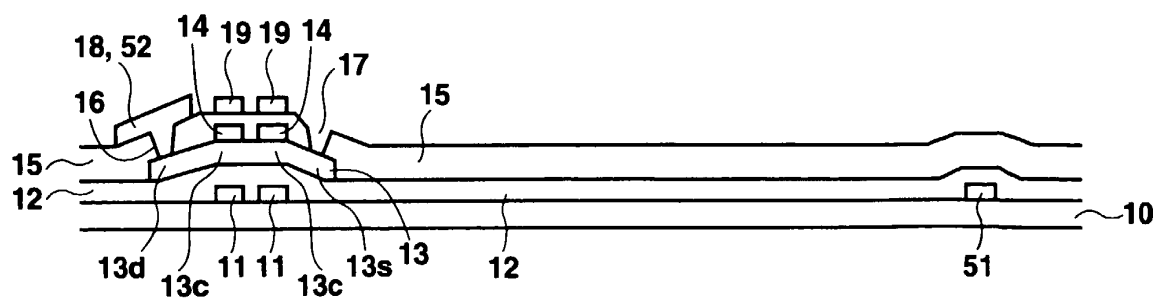


Fig. 3(a)

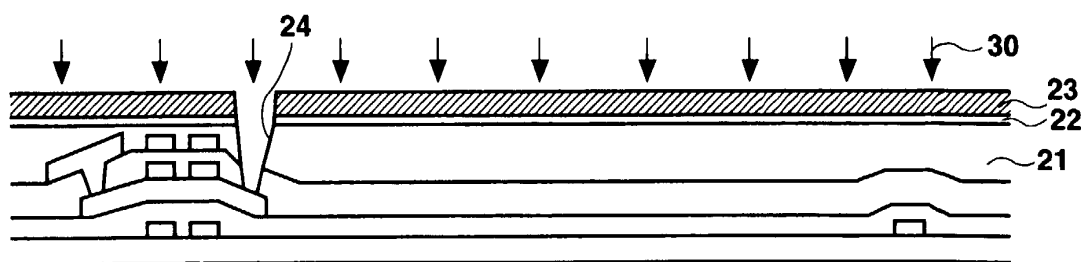


Fig. 3(b)

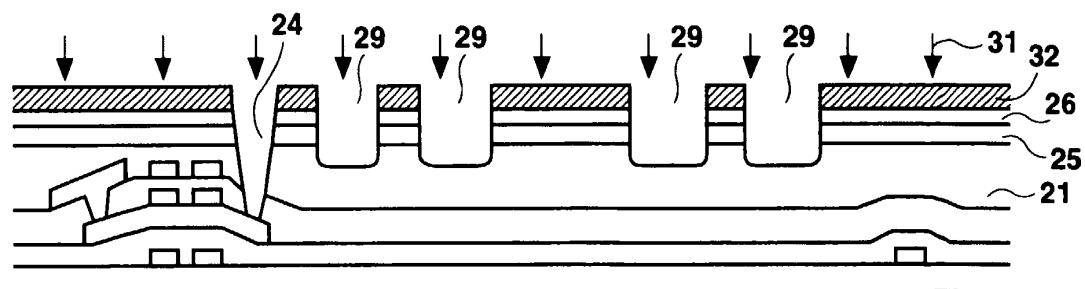


Fig. 3(c)

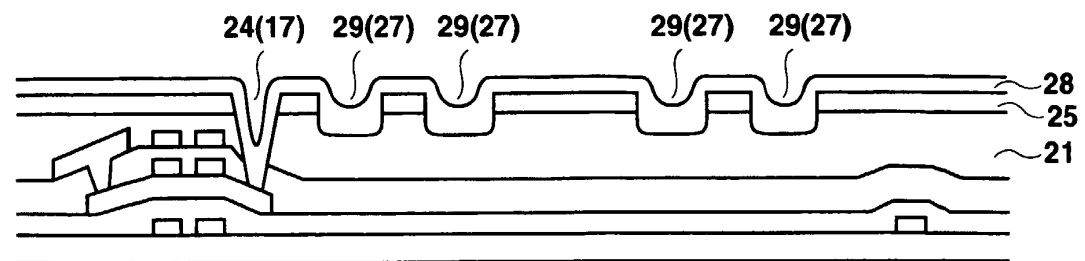


Fig. 3(d)

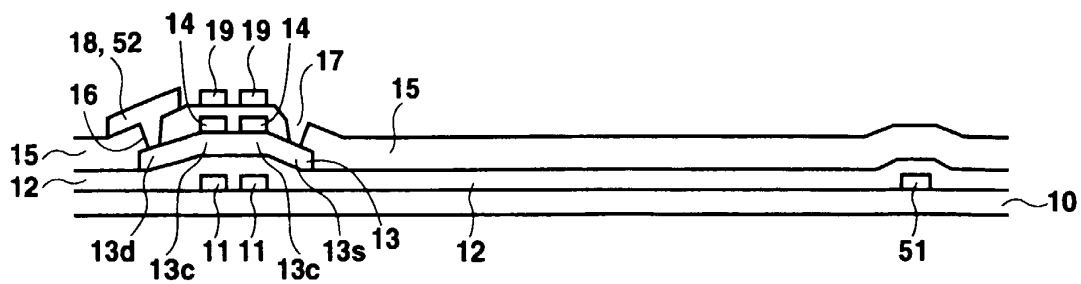


Fig. 4(a)

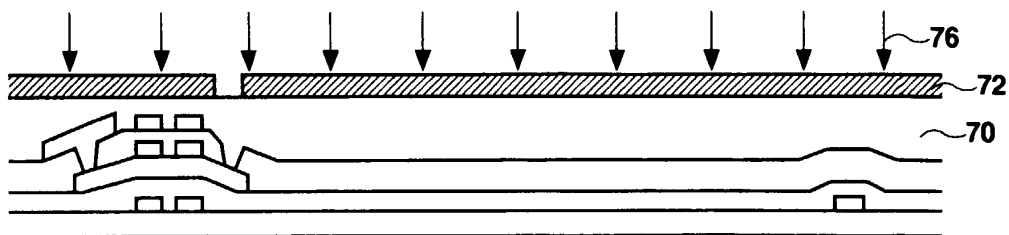


Fig. 4(b)

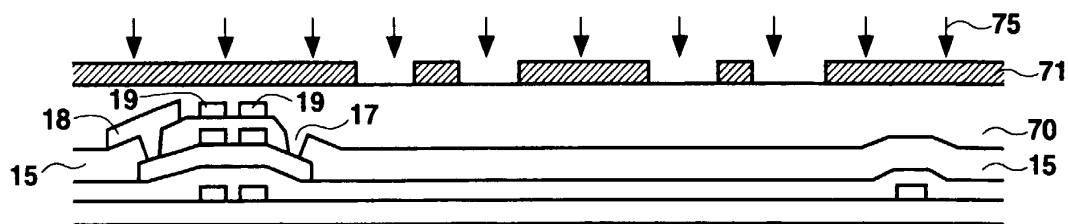


Fig. 4(c)

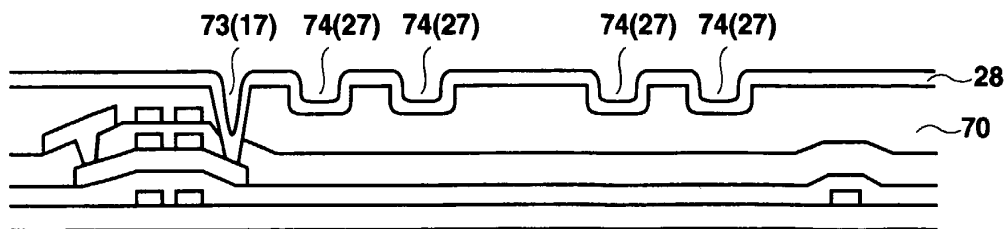


Fig. 4(d)

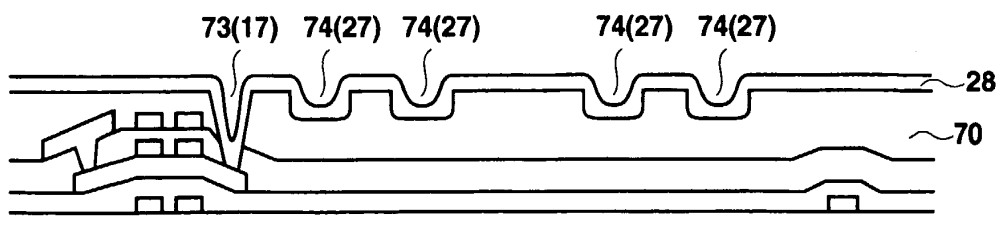


Fig. 4(e)

专利名称(译)	反射型液晶显示器的制造方法		
公开(公告)号	EP1069458A2	公开(公告)日	2001-01-17
申请号	EP2000305867	申请日	2000-07-12
[标]申请(专利权)人(译)	三洋电机株式会社		
申请(专利权)人(译)	SANYO ELECTRIC CO. , LTD.		
当前申请(专利权)人(译)	SANYO ELECTRIC CO. , LTD.		
[标]发明人	NORITAKE KAZUTO YAMAJI TOSHIFUMI		
发明人	NORITAKE, KAZUTO YAMAJI, TOSHIFUMI		
IPC分类号	G02F1/1335 G02F1/136 G02F1/1362 G02F1/1368 G09F9/30 G02F1/1333		
CPC分类号	G02F1/133553 G02F1/136227		
优先权	1999200600 1999-07-14 JP		
其他公开文献	EP1069458A3		
外部链接	Espacenet		

摘要(译)

在绝缘基板 (10) 上, 形成第一栅电极 (11), 栅极绝缘膜 (12), 半导体膜 (13) 和层间绝缘膜 (15)。在层间绝缘膜 (15) 上方, 形成 TFT, 其具有连接到第一栅电极 (11) 的第二栅电极 (17)。然后, 在现存层的整个表面上形成光敏树脂 (70)。随后, 使用第一掩模 (71) 施加第一次曝光 (75), 然后使用比第一次曝光所用的光量更大的第二掩模 (72) 施加第二次曝光 (76)。第二掩模 (72) 在对应于源 (13s) 的位置处具有开口。之后, 显影感光性树脂膜 (70), 形成接触孔 (73) 和凹部 (74)。

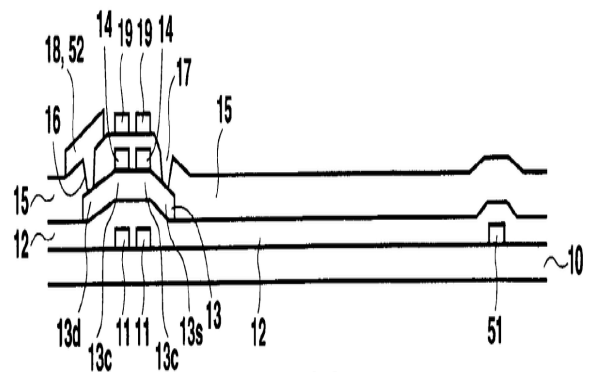


Fig. 1(a)